



VEC2602 — N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- Best suited for inverter applications.
- The VEC2602 incorporates an N-channel MOSFET and a P-channel MOSFET that feature low ON-resistance, thereby enabling high-density mounting.
- 4V drive.
- Mounting height 0.75mm.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		30	-30	V
Gate-to-Source Voltage	V _{GSS}		±20	±20	V
Drain Current (DC)	I _D		4	-3	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	16	-12	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm×X0.8mm)1unit	0.9		W
Total Dissipation	P _T	Mounted on a ceramic board (900mm×X0.8mm)	1.0		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D S=30V, V _{GS} =0			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _D S=0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _D S=10V, I _D =1mA	1.0		2.4	V
Forward Transfer Admittance	y _{fs}	V _D S=10V, I _D =2A	2.2	3.6		S
Static Drain-to-Source On-State Resistance	R _D S(on)1	I _D =2A, V _{GS} =10V		37	48	mΩ
	R _D S(on)2	I _D =1A, V _{GS} =4V		70	99	mΩ
Input Capacitance	C _{iss}	V _D S=10V, f=1MHz		370		pF
Output Capacitance	C _{oss}	V _D S=10V, f=1MHz		85		pF
Reverse Transfer Capacitance	C _{rss}	V _D S=10V, f=1MHz		47		pF

Marking : BE

Continued on next page.

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N1004PE TS IM TB-00000135 No.8021-1/6

VEC2602

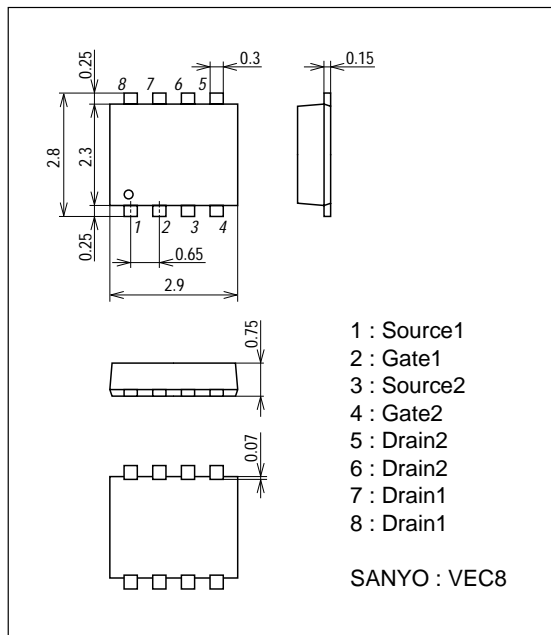
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		28		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		37		ns
Fall Time	t_f	See specified Test Circuit.		34		ns
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=10V, I_D=4A$		8.5		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=10V, I_D=4A$		1.8		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=10V, I_D=4A$		1.3		nC
Diode Forward Voltage	V_{SD}	$I_S=4A, V_{GS}=0$		0.83	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1mA, V_{GS}=0$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10V, I_D=-1mA$	-1.0		-2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-1.5A$	2.0	3.4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-1.5A, V_{GS}=-10V$		65	86	m Ω
	$R_{DS(on)2}$	$I_D=-0.7A, V_{GS}=-4V$		117	168	m Ω
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		510		pF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		115		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		78		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		17		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		53		ns
Fall Time	t_f	See specified Test Circuit.		35		ns
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-10V, I_D=-3A$		11		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-10V, I_D=-3A$		2.4		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-10V, I_D=-3A$		1.7		nC
Diode Forward Voltage	V_{SD}	$I_S=-3A, V_{GS}=0$		-0.87	-1.2	V

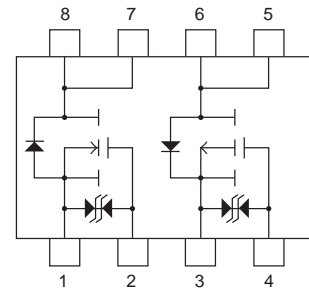
Package Dimensions

unit : mm

2227A



Electrical Connection



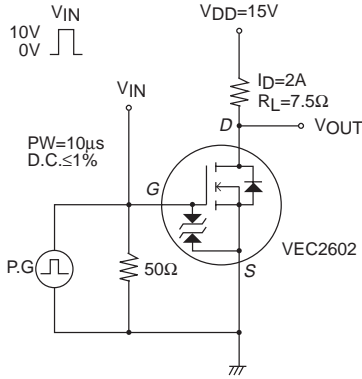
- 1 : Source1
- 2 : Gate1
- 3 : Source2
- 4 : Gate2
- 5 : Drain2
- 6 : Drain2
- 7 : Drain1
- 8 : Drain1

Top view

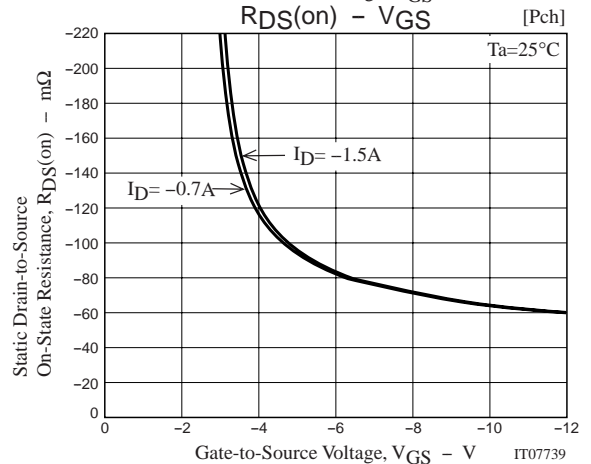
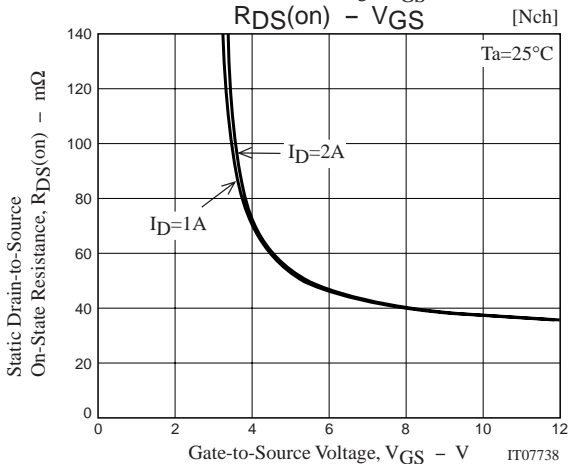
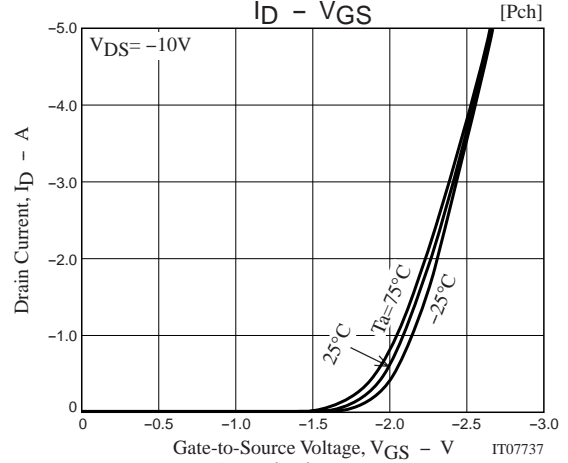
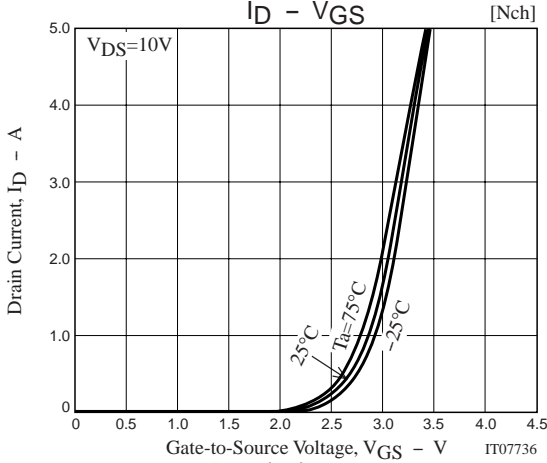
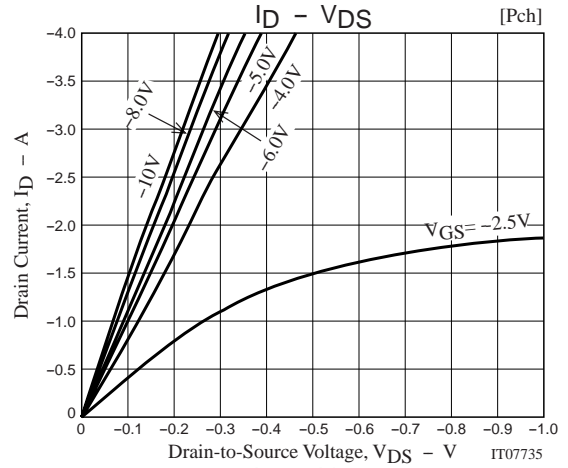
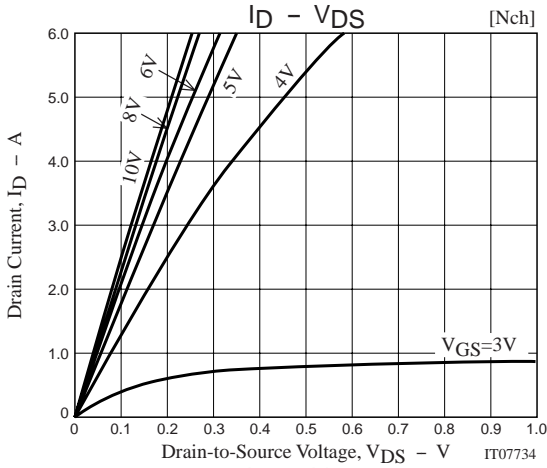
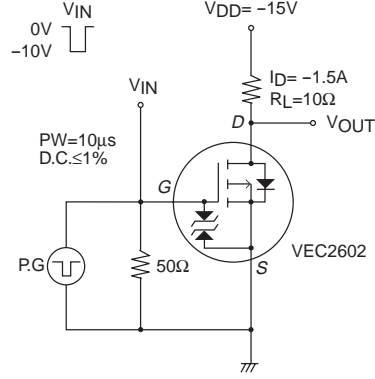
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Switching Time Test Circuit

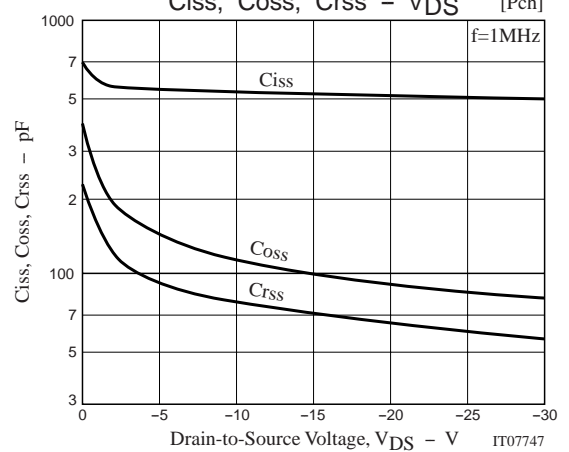
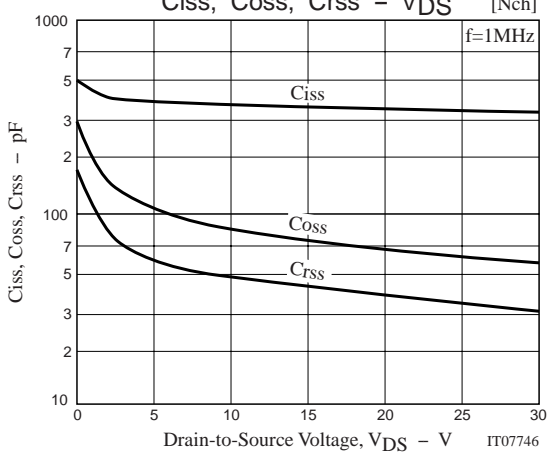
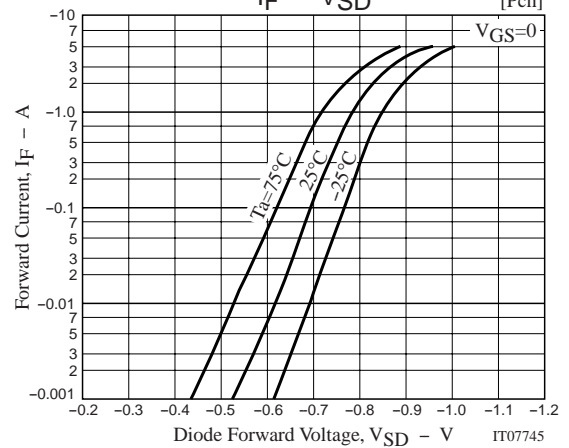
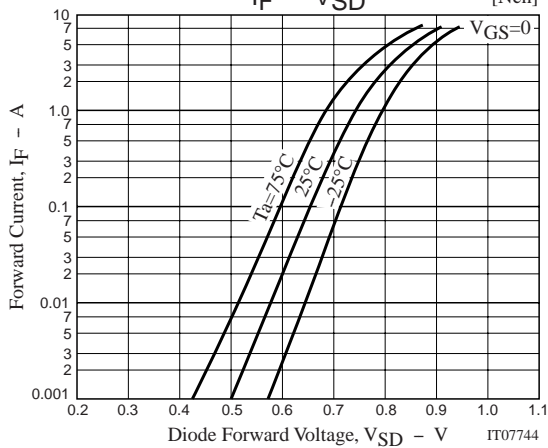
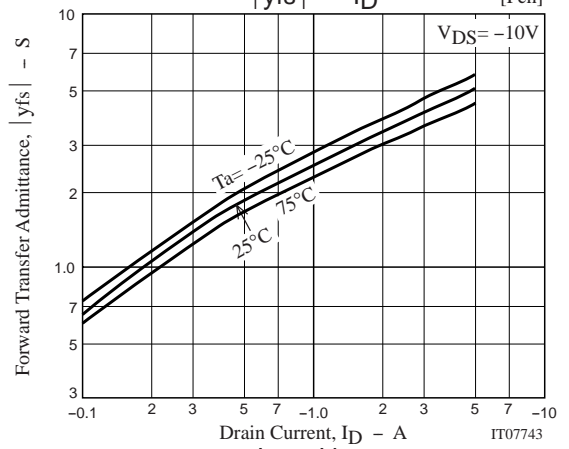
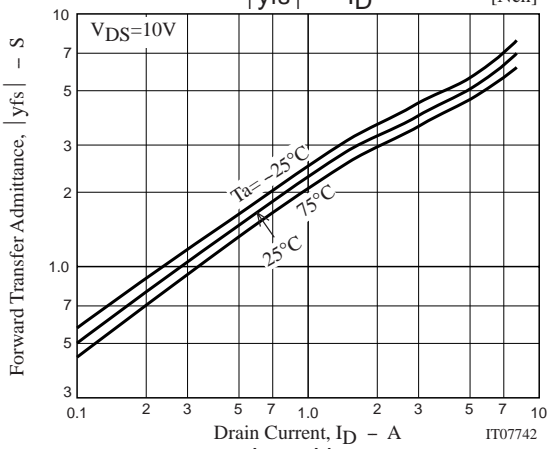
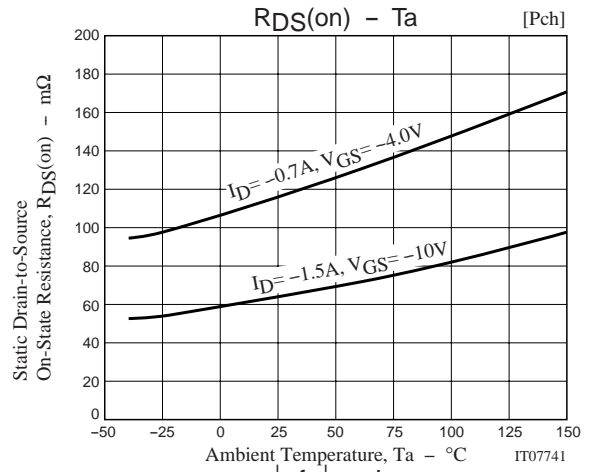
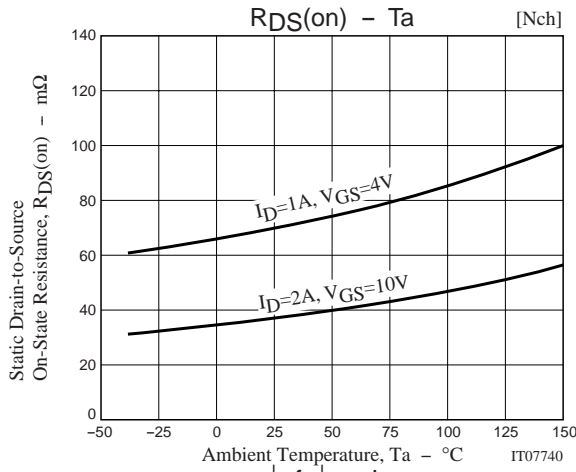
[N-channel]



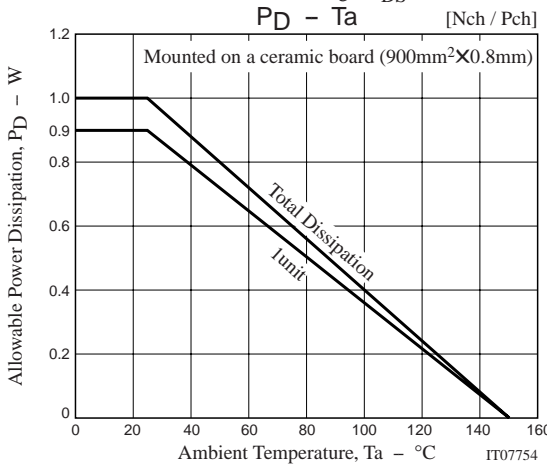
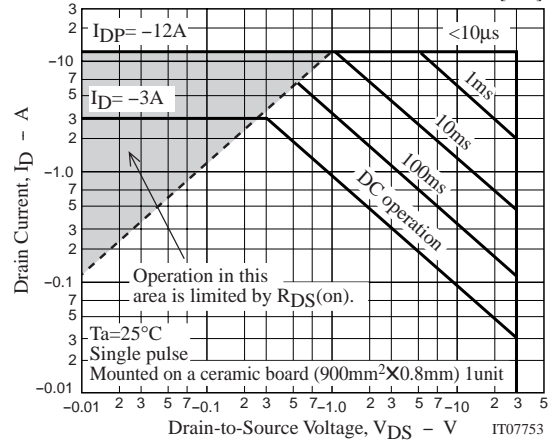
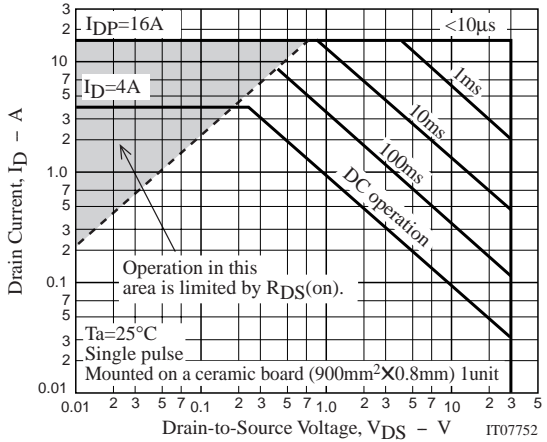
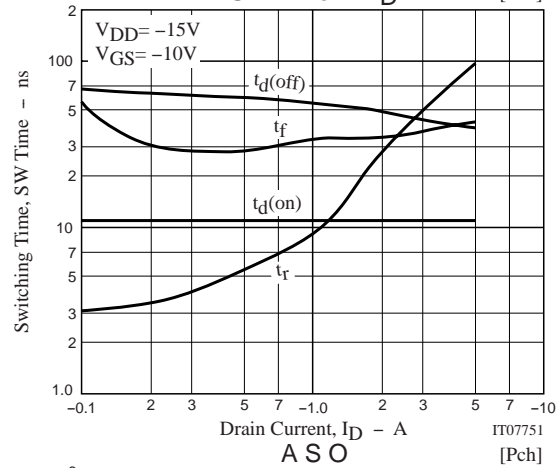
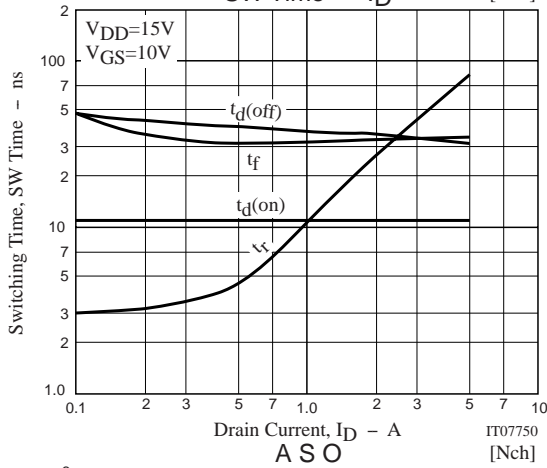
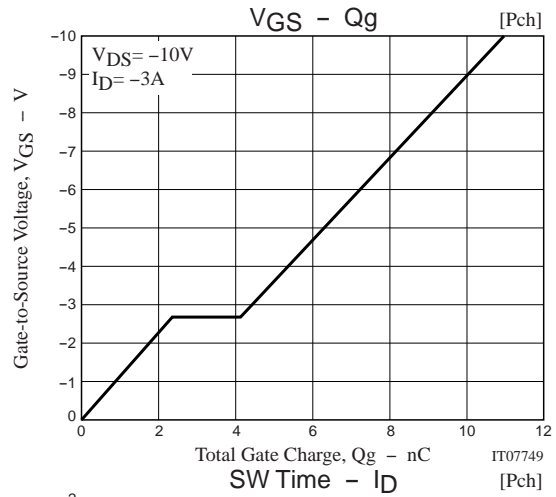
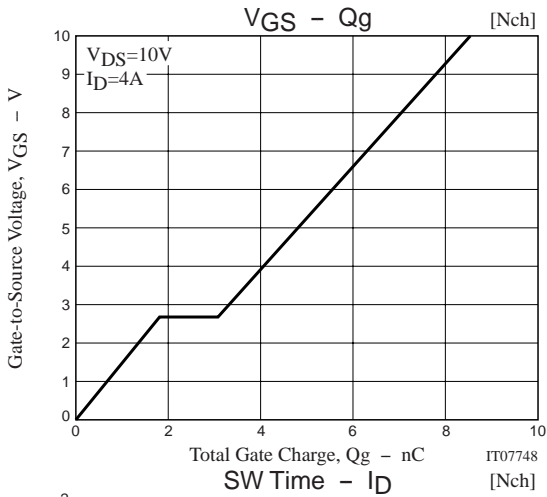
[P-channel]



VEC2602



VEC2602



Note on usage : Since the VEC2602 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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